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**B.Tech / M.Tech (Integrated) DEGREE EXAMINATION, JULY 2023**  
First / Second Semester

**21PYB102J - SEMICONDUCTOR PHYSICS AND COMPUTATIONAL METHODS**  
(For the candidates admitted from the academic year 2021-2022 & 2022-2023)

**Note:**

- (i) **Part - A** should be answered in OMR sheet within first 40 minutes and OMR sheet should be handed over to hall invigilator at the end of 40<sup>th</sup> minute.
- (ii) **Part - B** and **Part - C** should be answered in answer booklet.

Time: 3 Hours

Max. Marks: 75

**PART – A (20 × 1 = 20Marks)**

Answer **ALL** Questions

Marks    BL    CO    PO

- |  |   |   |   |   |   |
|--|---|---|---|---|---|
| 1. Choose the correct expression for the band gap ( $E_g$ ) of materials from the following?<br>(A) $E_g = E_c + E_v$<br>(C) $E_g = (E_c - E_v)/2$   | (B) $E_g = E_c - E_v$<br>(D) $E_g = (E_c + E_v)/2$                | 1 | 1 | 1 | 1 |
| 2. The range of wave number (k) for the first Brillouin zone is _____.<br>(A) $-\pi/a$ to $\pi/a$<br>(C) $-2\pi/a$ to $2\pi/a$   | (B) 0 to $\pi/a$<br>(D) 0 to $2\pi/a$                             | 1 | 1 | 1 | 1 |
| 3. In a metal, the electron always move _____ in the absence of electric field.<br>(A) With constant velocity<br>(C) With drift velocity   | (B) In the direction of electric field<br>(D) Randomly            | 1 | 2 | 1 | 1 |
| 4. Phonon is a quantum of _____.<br>(A) Lattice vibrations<br>(C) Magnetic energy  | (B) Electromagnetic energy<br>(D) Gravitational energy            | 1 | 2 | 1 | 1 |
| 5. In LED, what is the shape of domes made from plastics used to minimize the losses caused by bulk absorption thereby increasing the external efficiency?<br>(A) Spherical<br>(C) Hexagonal | (B) Octahedral<br>(D) Hemi spherical                              | 1 | 1 | 2 | 1 |
| 6. Auger generation/recombination is also known as _____.<br>(A) Two particle transitions<br>(C) Four particle transitions   | (B) Three particle transitions<br>(D) Single particle transitions | 1 | 1 | 2 | 1 |
| 7. If "n" and "p" denotes the number of electrons in the conduction and holes in the valence band, for an intrinsic semiconductor _____.<br>(A) $n > p$<br>(C) $n = p$                       | (B) $n < p$<br>(D) $n \geq p$                                     | 1 | 2 | 2 | 1 |

8. To obtain an p-type semiconductor, an intrinsic semiconductor is doped with which of the below? 1 2 2 1  
 (A) Phosphorous (B) Nitrogen  
 (C) Arsenic (D) Boron
9. If the number of upward transition per seconds exceeds the number of downward transition, \_\_\_\_\_ is achieved 1 2 3 3  
 (A) Optical gain (B) Optical loss  
 (C) Equilibrium (D) Absorption
10. Which of the below is an inter band transition? 1 1 3 3  
 (A) Impurity to band transition (B) Band to band transition  
 (C) Free carrier transition (D) Phonon transition
11. The generation of electron-hole pairs by the incidence of light followed by their radiative recombination is known as 1 2 3 3  
 (A) Photoluminescence (B) Electroluminescence  
 (C) Thermoluminescence (D) Cathodoluminescence
12. The Fermi's golden rule helps to identify the \_\_\_\_\_ 1 1 3 3  
 (A) Momentum of electrons (B) Velocity of light  
 (C) Absorption energy of electron (D) Transition rate per unit volume
13. If the Hall voltage is positive in, the sample is a \_\_\_\_\_. 1 2 4 1  
 (A) Insulator (B) n-type semiconductor  
 (C) Conductor (D) p-type semiconductor
14. If the measured voltage is positive in hot point probe method, the sample is a \_\_\_\_\_. 1 2 4 1  
 (A) n-type semiconductor (B) p-type semiconductor  
 (C) Insulator (D) Conductor
15. The resistance of a material is inversely proportional to the \_\_\_\_\_. 1 2 4 1  
 (A) Length<sup>2</sup> (B) Length  
 (C) Area of cross section (D) Area×Length
16. In four probe method, the outer two contacts are connected to \_\_\_\_\_. 1 2 4 1  
 (A) Galvanometer (B) Variable resistor  
 (C) Voltmeter (D) Current source
17. The notation for arm chair carbon nanotube can be written as \_\_\_\_\_. 1 1 5 3  
 (A) (n, 0) (B) (n, n)  
 (C) (n, m) (D) (0, m)
18. High resolution Transmission electron microscopy helps us to see the \_\_\_\_\_ of the sample. 1 1 5 3  
 (A) Inside (B) Surface texture  
 (C) Atoms/Planes (D) Electrons
19. In a 1D material, the density of states is \_\_\_\_\_. 1 2 5 3  
 (A) Proportional to  $E^{-1/2}$  (B) Proportional to  $E^{1/2}$   
 (C) Independent of E (D) Proportional to  $E^2$

20. The material size is reduced in one direction and the electron can move freely only in two directions in \_\_\_\_\_.  
 (A) Bulk (B) Quantum dot  
 (C) Thin sheets (D) Quantum wire

**PART – B (5 × 8 = 40 Marks)**

Answer ALL Questions

- |   | Marks | BL | CO | PO |
|---|-------|----|----|----|
| 21. a. Deduce an expression of the density of states (DOS) of electrons in a 3-dimensional material.  | 8     | 3  | 1  | 1  |
| <b>(OR)</b>   |       |    |    |    |
| b. What are the assumptions of classical free electron theory? Write any two merits and demerits of this theory.  | 8     | 3  | 1  | 1  |
| 22. a. What is continuity equation? Derive the continuity equations for electrons in one dimensional semiconductor.                                       | 8     | 4  | 2  | 1  |
| <b>(OR)</b>   |       |    |    |    |
| b. What is OLED? Describe the structure of OLED with necessary diagram.   | 8     | 4  | 2  | 1  |
| 23. a. What are spontaneous and stimulated emissions? Obtain the relation between Einstein coefficients of spontaneous and stimulated emissions.          | 8     | 3  | 3  | 3  |
| <b>(OR)</b>   |       |    |    |    |
| b. Define optical joint density of states. Derive the expression for optical joint density of states.   | 8     | 3  | 3  | 3  |
| 24. a. What is Four point probe method? Explain how to measure the resistivity of a given material using linear four-probe technique with neat schematic. | 8     | 3  | 4  | 1  |
| <b>(OR)</b>   |       |    |    |    |
| b. Explain the Hall effect with a schematic diagram. Derive the expression for Hall coefficient of a p-type semiconductor.                                | 8     | 3  | 4  | 1  |
| 25. a. Discuss the classifications of carbon nanotubes according to the geometry. Also write their applications.  | 8     | 3  | 5  | 3  |
| <b>(OR)</b>   |       |    |    |    |
| b. Discuss in details about the preparation of nanomaterials using chemical vapour deposition (CVD) technique with appropriate schematic.                 | 8     | 3  | 5  | 3  |

**PART – C (1 × 15 = 15 Marks)**

Answer ANY ONE Question

- |   | Marks | BL | CO | PO |
|---|-------|----|----|----|
| 26. Explain the construction and working principle of scanning electron microscope (SEM) with neat schematic. Differentiate between SEM and TEM.        | 15    | 4  | 5  | 3  |
| 27. Discuss about Fermi's golden rule. Deduce the expression for the net upward transition rate ( $R_n$ ) in a semiconductor using Fermi's golden rule. | 15    | 4  | 3  | 3  |

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